Preferred Device

Low Noise Transistor

NPN Silicon

Features

• These are Pb–Free Devices*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	45	Vdc
Collector-Base Voltage	V _{CBO}	45	Vdc
Emitter-Base Voltage	V _{EBO}	6.5	Vdc
Collector Current – Continuous	Ι _C	200	mAdc
Total Device Dissipation @ $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	PD	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25^{\circ}C$ Derate above $25^{\circ}C$	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient (Note 1)	R_{\thetaJA}	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

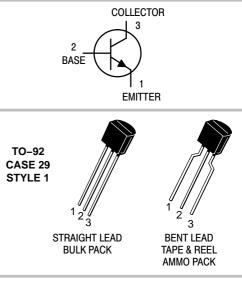
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. R_{0JA} is measured with the device soldered into a typical printed circuit board.

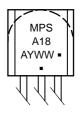


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MARKING DIAGRAM



A = Assembly Location

Y = Year

WW = Work Week

= Pb–Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
MPSA18G	TO-92 (Pb-Free)	5000 Units / Bulk
MPSA18RLRAG	TO–92 (Pb–Free)	2000/Tape & Reel
MPSA18RLRMG	TO-92 (Pb-Free)	2000/Ammo Pack

⁺For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use

and best overall value.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	·				
Collector – Emitter Breakdown Voltage (Note 2) ($I_C = 10 \text{ mAdc}, I_B = 0$)	V _{(BR)CEO}	45	_	_	Vdc
Collector – Base Breakdown Voltage $(I_C = 100 \ \mu Adc, I_E = 0)$	V _{(BR)CBO}	45	_	_	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10 \ \mu Adc, I_C = 0$)	V _{(BR)EBO}	6.5	_	_	Vdc
Collector Cutoff Current ($V_{CB} = 30 \text{ Vdc}, I_E = 0$)	I _{CBO}	_	1.0	50	nAdc
ON CHARACTERISTICS (Note 2)	·				
$ \begin{array}{l} \text{DC Current Gain} \\ (I_{C} = 10 \ \mu \text{Adc}, \ V_{CE} = 5.0 \ \text{Vdc}) \\ (I_{C} = 100 \ \mu \text{Adc}, \ V_{CE} = 5.0 \ \text{Vdc}) \\ (I_{C} = 1.0 \ \text{mAdc}, \ V_{CE} = 5.0 \ \text{Vdc}) \\ (I_{C} = 10 \ \text{mAdc}, \ V_{CE} = 5.0 \ \text{Vdc}) \\ (I_{C} = 10 \ \text{mAdc}, \ V_{CE} = 5.0 \ \text{Vdc}) \end{array} $	h _{FE}	400 500 500 500	580 850 1100 1150	- - - 1500	-
Collector – Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}, I_B = 0.5 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc}$)	V _{CE(sat)}		_ 0.08	0.2 0.3	Vdc
Base – Emitter On Voltage (I _C = 1.0 mAdc, V _{CE} = 5.0 Vdc)	V _{BE(on)}	_	0.6	0.7	Vdc
SMALL-SIGNAL CHARACTERISTICS	·	•			
Current–Gain – Bandwidth Product ($I_C = 1.0 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc}, f = 100 \text{ MHz}$)	f _T	100	160	_	MHz
Collector–Base Capacitance $(V_{CB} = 5.0 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$	C _{cb}	_	1.7	3.0	pF
Emitter–Base Capacitance ($V_{EB} = 0.5 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz}$)	C _{eb}	_	5.6	6.5	pF
Noise Figure (I _C = 100 μAdc, V _{CE} = 5.0 Vdc, R _S = 10 kΩ, f = 1.0 kHz) (I _C = 100 μAdc, V _{CE} = 5.0 Vdc, R _S = 1.0 kΩ, f = 100 Hz)	NF		0.5 4.0	1.5 -	dB
Equivalent Short Circuit Noise Voltage (I _C = 100 μ Adc, V _{CE} = 5.0 Vdc, R _S = 1.0 kΩ, f = 100 Hz)	V _T	_	6.5	_	nV/√H

2. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.

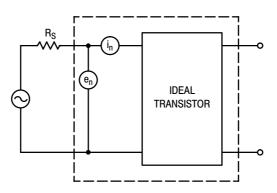
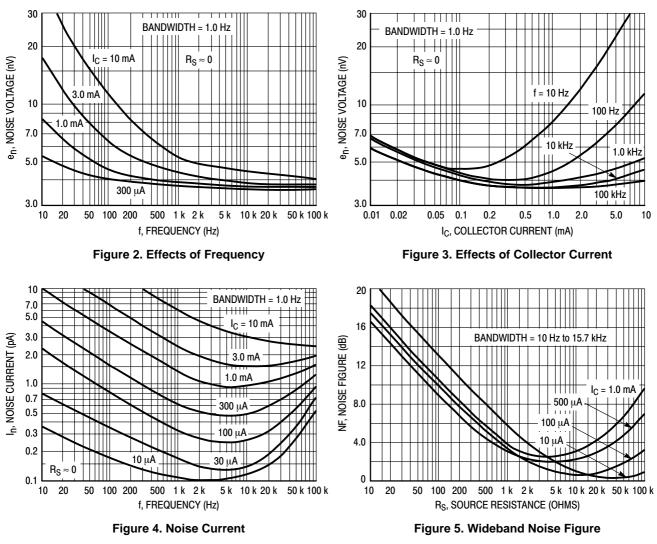


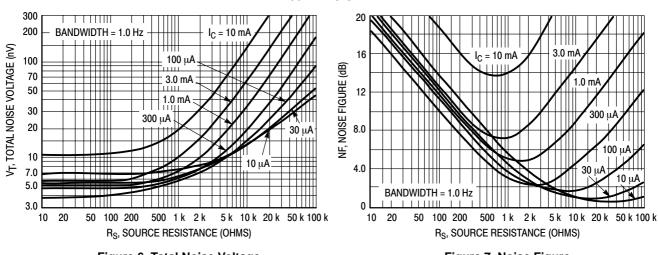
Figure 1. Transistor Noise Model

NOISE CHARACTERISTICS

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}C)$

NOISE VOLTAGE





100 Hz NOISE DATA

Figure 6. Total Noise Voltage



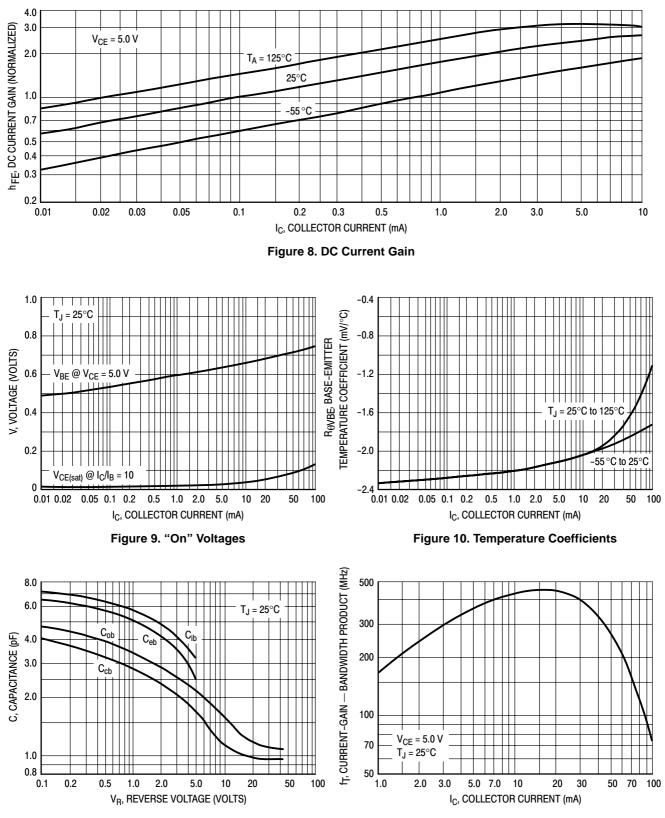
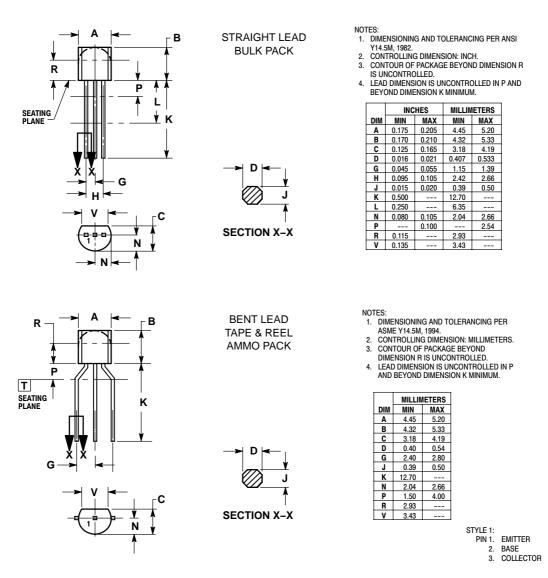


Figure 11. Capacitance

Figure 12. Current–Gain – Bandwidth Product

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 ISSUE AM



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